

MA2C188

Silicon epitaxial planar type

For high speed and high voltage switching, small-power rectification

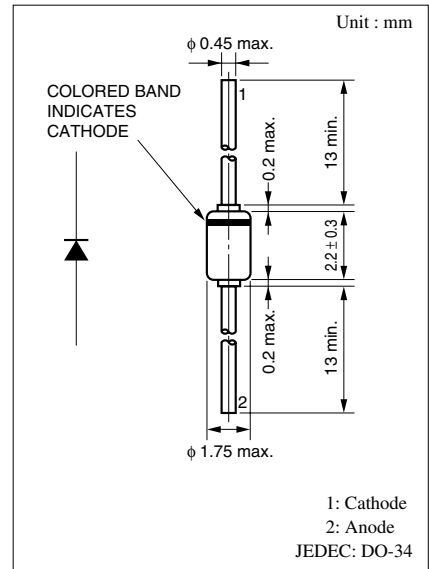
■ Features

- Small glass type (DO-34) package, allowing to insert into a 5 mm pitch hole
- High voltage (V_R : 200 V) rectification is possible

■ Absolute Maximum Ratings $T_a = 25^\circ\text{C}$

Parameter	Symbol	Rating	Unit
Reverse voltage (DC)	V_R	200	V
Peak reverse voltage	V_{RM}	250	V
Average power dissipation	$P_{F(AV)}$	400	mW
Output current	I_O	200	mA
Repetitive peak forward current	I_{FRM}	625	mA
Non-repetitive peak forward surge current*	I_{FSM}	1	A
Junction temperature	T_j	175	$^\circ\text{C}$
Storage temperature	T_{stg}	-65 to +175	$^\circ\text{C}$

Note) * : $t = 1$ s



■ Electrical Characteristics $T_a = 25^\circ\text{C}$

Parameter	Symbol	Conditions	Min	Typ	Max	Unit
Reverse current (DC)	I_R	$V_R = 200$ V			200	nA
Forward voltage (DC)	V_F	$I_F = 200$ mA			1.2	V
Reverse voltage (DC)	V_R	$I_R = 100$ μA	250			V
Terminal capacitance	C_t	$V_R = 0$ V, $f = 1$ MHz		1.0		pF
Reverse recovery time*	t_{rr}	$I_F = 10$ mA, $V_R = 1$ V $I_{rr} = 0.1 \cdot I_R$, $R_L = 100$ Ω			60	ns

Note) 1. Rated input/output frequency: 20 MHz

2. * : t_{rr} measuring circuit

